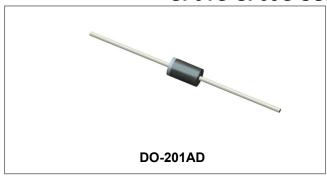






SF31G-SF38G SUPER FAST RECTIFIER



Features

- · Super fast switching for high efficiency
- Low leakage current
- High forward surge capability
- Solder dip 260 ° C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: JEDEC DO-201AD molded plastic body
- Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 1.02 gram

Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Characteristic	Symbol	SF31G	SF32G	SF33G	SF34G	SF35G	SF36G	SF38G	Units
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	150	200	300	400	600	V
Maximum RMS voltage	V _{RMS}	35	70	105	140	210	280	420	V
Maximum DC blocking voltage	V _{DC}	50	100	150	200	300	400	600	V
Maximum average forward rectified current 0.375"(9.5mm) lead length at T_A =55 $^{\circ}$ C	I _(AV)	3.0				А			
Peak forward surge current 8.3ms single half sinewave superimposed on rated load (JEDEC Method)	I _{FSM}	125.0				А			
Maximum instantaneous forward voltage at 3.0A	V _F	0.95 1.25			1.7	V			
Maximum DC reverse current T_A =25 $^{\circ}$ C at rated DC blocking voltage T_A =100 $^{\circ}$ C	I _R	5.0 50.0			μA				
Maximum Reverse Recovery Time (Note 1)	Trr	35			ns				
Typical Junction Capacitance (Note 2)	Сл	100.0			50.0		pF		
Typical Thermal Resistance (Note 3)	$R_{\theta JA}$	30.0			°C/W				
Junction Temperature	TJ	-65 to +150					°C		
Storage Temperature Range	T _{STG}	-65 to +150				°C			

Note: 1. Reverse recovery condition IF=0.5A, IR=1.0A. Irr=0.25A

- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
- 3. Thermal resistance from junction to ambient at 0.375"(9.5mm) lead length, P.C.B mounted.
 - China Germany Korea Singapore United States
 - http://www.smc-diodes.com
 sales@ smc-diodes.com

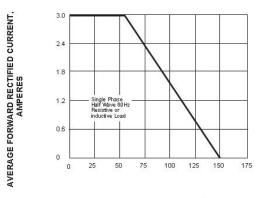






Ratings and Characteristics Curves

FIG. 1- FORWARD CURRENT DERATING CURVE



AMBIENT TEMPERATURE,°C

FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

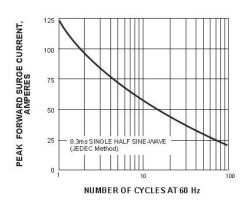
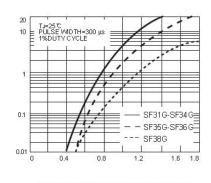


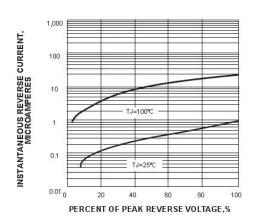
FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS





INSTANTANEOUS FORWARD VOLTAGE, VOLTS

FIG. 4-TYPICAL REVERSE CHARACTERISTICS



[•] China - Germany - Korea - Singapore - United States •

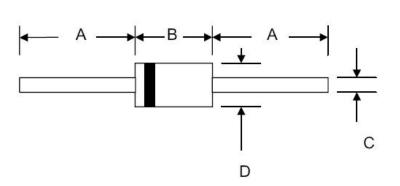
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Mechanical Dimensions DO-201AD



SYMBOL	Millim	neters	Inches			
STWIBOL	Min.	Max.	Min.	Max.		
А	25.4	-	1.000	-		
В	8.50	9.50	0.335	0.374		
С	1.2	1.3	0.048	0.052		
D	5.0	5.6	0.197	0.220		

Ordering Information

Device	Package	Shipping
SF31G THRU SF38G	DO-201AD (Pb-Free)	1250pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



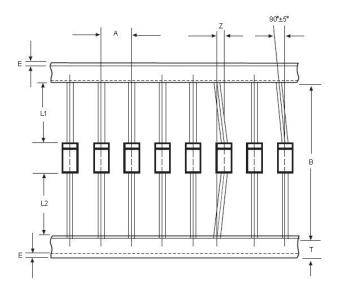
Where XXXXX is YYWWL

SF31G SSG YY WW = Part Name = SSG

= Year / = Week

= Lot Number

Carrier Tape Specification DO-201AD



SYMBOL	Millimeters			
STWIBOL	Min.	Max.		
А	9.50	10.50		
В	50.9	53.9		
Z	-	1.20		
Т	5.60	6.40		
Е	-	0.80		
IL1-L2I	-	1.0		

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